

Handbook of Thin Film Materials

Volume 4

Semiconductor and Superconductor Thin Films

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Contents

About the Editor	xix
List of Contributors	xxi
Volume Listing	xxiii

Chapter 1. ELECTROCHEMICAL PASSIVATION OF Si AND SiGe SURFACES

J. Rappich, Th. Dittrich

1. Introduction	2
2. In Situ Characterization of Surface Bond Configurations and Electronic Surface States	3
2.1. Fourier Transform Infrared Spectroscopy–Attenuated Total Reflection	3
2.2. Pulsed Surface Photovoltage	6
2.3. Pulsed Photoluminescence	9
3. Electrochemically Hydrogenated Si Surfaces	12
3.1. Electrochemical Hydrogenation in Diluted HF Solutions	13
3.2. Hydrogenated Si Surfaces in Alkaline Solutions	16
3.3. Electronic States at Hydrogenated Si Surfaces	17
3.4. Role of the Etch Rate for Surface State Formation	19
3.5. Local Reconstruction and Origin of Surface States	21
4. Hydrogenated Porous Silicon	22
4.1. pH Dependence of the Formation of Ultrathin Porous Si	23
4.2. Competition between Hydrogenation and Electropolishing	26
4.3. Electronic States at Internal Surfaces of Porous Si and Local Reconstruction	29
5. Thin Anodic Oxides on Si	31
5.1. Initial States of Anodic Oxidation	31
5.2. Passivation by Electron Injection at Cathodic Potentials	34
5.3. Passivation by Process Optimization at Anodic Potentials	36
5.4. Formation of Oxides in Alkaline Solution	40
6. Thick Anodic Oxides on Si	41
6.1. Low Thermal Budget Processing	41
6.2. Preparation of the Oxide Layer	42
6.3. Electronic Characterization	43
6.4. Passivation of Steps and Trenches	44
7. Enhanced Passivation of SiGe by Anodic Oxidation	46
7.1. Defect Concentration at the Oxide/c-SiGe Interface	46
7.2. Morphology of Oxidized epi-SiGe Samples	48
7.3. Oxide Composition	48
7.4. Photoluminescence Spectra of Oxidized SiGe Layers	50
7.5. Conclusions and Outlook	51
Acknowledgments	52
References	52

Chapter 2. EPITAXIAL GROWTH AND STRUCTURE OF III-V NITRIDE THIN FILMS

Dharanipal Doppalapudi, Theodore D. Moustakas

1. Introduction	57
2. Growth Methods	59
2.1. Growth of GaN and AlN Bulk Crystals	60
2.2. Hydride Vapor Phase Epitaxy	60

2.3. Metal Organic Vapor Deposition	62
2.4. Molecular Beam Epitaxy	64
3. Epitaxial Growth	67
3.1. Homoepitaxial Growth	67
3.2. Heteroepitaxial Growth	68
4. Doping of III-Nitrides	87
4.1. Unintentionally Doped Films	87
4.2. Films with <i>n</i> -Type Doping	88
4.3. Films with <i>p</i> -Type Doping	89
4.4. Doping of InGaN and AlGaN Films	90
5. Structure and Microstructure of Epitaxial GaN	90
5.1. Residual Stresses	91
5.2. Polarity	92
5.3. Polytype Defects	95
5.4. Dislocations	96
6. Ternary Alloys	100
6.1. InGaN Alloys	100
6.2. AlGaN Alloys	108
References	111

Chapter 3. OPTICAL PROPERTIES OF HIGHLY EXCITED (Al, In) GaN EPILAYERS AND HETEROSTRUCTURES

Sergiy Bidnyk, Theodore J. Schmidt, Jin-Joo Song

1. Introduction	118
1.1. Historical Perspective and Economic Projections	118
1.2. Challenges in Nitride Thin Film Research and Development	120
1.3. Chapter Organization	121
2. General Optical Properties of the Group III-Nitrides	121
2.1. Physical Properties and Band Structure	121
2.2. Photoluminescence	122
2.3. Strain Considerations	123
2.4. Absorption	123
2.5. Reflection and Photoreflectance	124
3. Pump-Probe Spectroscopy of Highly Excited Group III-Nitrides	125
3.1. Introduction to Pump-Probe Spectroscopy	125
3.2. Single-Beam Power-Dependent Absorption Spectroscopy of GaN Thin Films	126
3.3. Nondegenerate Optical Pump-Probe Absorption Spectroscopy of GaN Thin Films at Zero Time Delay	126
3.4. Nanosecond Experiments at Nonzero Time Delay	129
3.5. Femtosecond Experiments	131
3.6. Pump-Probe Reflection Spectroscopy of GaN Thin Films	134
3.7. Pump-Probe Absorption Spectroscopy of InGaN Thin Films	135
3.8. Summary	136
4. Gain Mechanisms in Nitride Lasing Structures	137
4.1. Overview of Gain Mechanisms	137
4.2. Origin of Stimulated Emission in GaN Epilayers	138
4.3. Mechanism of Efficient Ultraviolet Lasing in GaN/AlGaN Separate Confinement Heterostructures	141
4.4. Gain Mechanism in AlGaN Thin Films	145
5. Optical Properties of InGaN-Based Heterostructures	147
5.1. Physical Properties of InGaN Thin Films and Heterostructures	147
5.2. Fundamental Optical Properties of InGaN-Based Structures	149
5.3. Influence of In Composition in InGaN Layers	153
5.4. Influence of Silicon Doping in GaN Barriers	154
5.5. Optical Transitions at Various Temperatures and Excitation Conditions	157
5.6. Excitation Condition Dependence of Optical Transition	159
5.7. Excitation Length Dependence of Stimulated Emission	163
5.8. Summary of Optical Properties of InGaN	165

6.	Optical Properties of Nitride Thin Films at High Temperatures	166
6.1.	High-Temperature Stimulated Emission and Damage Mechanisms in GaN Epilayers	166
6.2.	Stimulated Emission in InGaN/GaN Multiple Quantum Wells at Elevated Temperatures	169
7.	Microstructure Lasing	172
7.1.	Origin of Surface-Emitted Stimulated Emission in GaN Epilayers	172
7.2.	Effects of Microcracks on the Lasing Characteristics of Nitride Thin Films	174
7.3.	Ring-Cavity Lasing in Laterally Overgrown GaN Pyramids	175
8.	Imaging Techniques for Wide-Bandgap Semiconductors	178
8.1.	Transverse Lasing Modes in GaN-Based Lasing Structures	178
8.2.	Novel Technique for Evaluating Optical Confinement in GaN-Based Lasing Structures	179
9.	Summary	182
	Acknowledgments	183
	References	183

Chapter 4. ELECTRICAL CONDUCTION PROPERTIES OF THIN FILMS OF CADMIUM COMPOUNDS

R. D. Gould

1.	Introduction	187
2.	Structure	189
2.1.	Cadmium Sulfide	190
2.2.	Cadmium Telluride	193
2.3.	Cadmium Selenide	195
2.4.	Cadmium Arsenide	198
3.	Electrical Properties	202
3.1.	Band Structure	202
3.2.	Lateral Resistivity	208
3.3.	High Field Dc Conductivity	220
3.4.	Ac Conductivity	235
4.	Summary and Conclusions	242
	Acknowledgments	243
	References	244

Chapter 5. CARBON-CONTAINING HETEROEPITAXIAL SILICON AND SILICON/GERMANIUM THIN FILMS ON Si(001)

H. Jörg Osten

1.	Introduction	247
2.	Growth of Epitaxial $\text{Si}_{1-y}\text{C}_y$ and $\text{Si}_{1-x-y}\text{Ge}_x\text{C}_y$	248
2.1.	Basic Considerations	248
2.2.	The Concept of Surface Solubility	249
2.3.	Substitutional versus Interstitial C Incorporation	250
2.4.	Segregation of Carbon-Containing Complexes	253
2.5.	Substitutional Carbon Incorporation during $\text{Si}_{1-x-y}\text{Ge}_x\text{C}_y$: Dependence on Germanium and Carbon	254
3.	Mechanical and Structural Properties	256
3.1.	Strain Manipulation	256
3.2.	Microscopic Structure of $\text{Si}_{1-x-y}\text{Ge}_x\text{C}_y$ Alloys	257
3.3.	Strain-Compensated Ternary Alloys	260
3.4.	Strain Relaxation in Tensile Strained $\text{Si}_{1-y}\text{C}_y$ Layers on Si(001)	261
3.5.	Strain Relaxation of Ternary Alloys	265
3.6.	Relaxed $\text{Si}_{1-x}\text{Ge}_x/\text{Si}_{1-x-y}\text{Ge}_x\text{C}_y$ Buffer Structures with Low Threading Dislocation Density	266
4.	Electrical Properties of C-Containing Alloys on Si(001)	268
4.1.	Band Gap Changes and Band Offsets	268
4.2.	Charge Transport	273

5. Highly Concentrated Pseudomorphic $\text{Si}_{1-y}\text{C}_y$ Layers	277
5.1. Model Considerations	277
5.2. Experimental Verification	278
5.3. Formation of a Carbon-Rich Surface on Silicon	278
6. Device Application of SiGe:C	280
6.1. Control of Dopant Diffusion by the Addition of Low Carbon Concentrations	280
6.2. Effect of Carbon on Boron Diffusion	281
6.3. SiGe:C Heterojunction Bipolar Transistor	282
6.4. SiGe:C HBT Results	285
7. Summary and Outlook	288
Acknowledgments	288
References	288

**Chapter 6. LOW-FREQUENCY NOISE SPECTROSCOPY FOR
CHARACTERIZATION OF POLYCRYSTALLINE
SEMICONDUCTOR THIN FILMS AND POLYSILICON
THIN FILM TRANSISTORS**

Charalabos A. Dimitriadis, George Kamarinos

1. Introduction	291
1.1. Definitions and Noise Sources	291
1.2. $1/f$ Noise in Semiconductors	292
1.3. $1/f$ Noise in MOSFETs	293
1.4. The Present Work	294
2. Noise of Polycrystalline Semiconductor Thin Films	294
2.1. Introduction	294
2.2. Noise Model	294
2.3. Application in β -FeSi ₂ Films	296
3. Noise of the Drain Current in Polysilicon TFTs	298
3.1. Introduction	298
3.2. Empirical Relationship Between Noise and Grain Boundary Barrier Height	298
3.3. Grain Boundary Barrier Height Inhomogeneities	300
3.4. Noise Spectroscopy for Grain Boundary and Interface Trap Characterization	302
3.5. Verification of the Noise Model	304
3.6. Application in Excimer Laser-Annealed Polysilicon TFTs	307
3.7. Correlation Between Noise and Static Device Parameters	308
3.8. Noise of Very Thin Excimer Laser-Annealed Polysilicon TFTs	311
4. Noise of the Leakage Current in Polysilicon TFTs	313
4.1. Introduction	313
4.2. Conduction Measurements	313
4.3. Noise Measurements	316
5. Avalanche-Induced Excess Noise in Polysilicon TFTs	318
6. Hot-Carrier Phenomena in Polysilicon TFTs	320
7. Concluding Remarks	323
References	324

**Chapter 7. GERMANIUM THIN FILMS ON SILICON FOR DETECTION OF
NEAR-INFRARED LIGHT**

G. Masini, L. Colace, G. Assanto

1. Introduction	327
1.1. The Scenario	327
1.2. Near-Infrared Detectors	329
2. SiGe Technology	330
2.1. Heteroepitaxy of SiGe	330
2.2. SiGe for Near-Infrared Detection	332

2.3. Relaxed SiGe Films: A Brief Overview	333
2.4. Relaxed SiGe Films: Recent Approaches	338
3. SiGe on Si NIR Photodetectors: Historical Overview	346
3.1. Early Devices	346
3.2. The Work at Bell Labs	347
3.3. European Efforts	349
3.4. The Introduction of SiGeC	351
3.5. Optimized Waveguide Photodetectors	351
3.6. Toward Operation at 1.55 μm	352
3.7. An Integrated Detector-Modulator	354
3.8. Polycrystalline Ge Detectors	355
3.9. Conclusions	356
4. Functional Devices	356
4.1. Voltage Tunable Detectors	356
4.2. Array of NIR Photodetectors	358
4.3. A NIR Wavemeter Integrated on Si	359
4.4. Conclusions	361
Appendix: Numerical Simulation of Relaxed Ge/Si Heterojunctions	361
A.1. Ge/Si Heterojunctions	361
A.2. Electric Equivalent of Relaxed Ge/Si Heterointerfaces	362
A.3. Band Diagrams, Current-Voltage, and Wavelength Responses	363
References	365

Chapter 8. PHYSICAL PROPERTIES OF AMORPHOUS GALLIUM ARSENIDE

Roberto Murri, Nicola Pinto

1. Introduction	369
2. Deposition and Growth Parameters	370
2.1. Dc and Rf Sputtering	370
2.2. Flash Evaporation	373
2.3. Other Methods of Deposition	374
3. Composition, Structural, and Morphological Properties	375
3.1. Theoretical Results	375
3.2. Experimental Results	375
4. Density of States	379
4.1. Models, Calculations, and Theoretical Results	379
4.2. Experimental Results	383
5. Optical Properties	385
5.1. Theoretical Results	385
5.2. Experimental Results	385
6. Phonon Spectra	388
6.1. Theoretical Results	388
6.2. Experimental Results	389
7. Electrical Transport Properties	391
7.1. Dc and Rf Sputtering	391
7.2. Flash Evaporation	395
7.3. Other Methods of Deposition	397
8. Applications, Devices	398
9. List of Symbols	399
References	400

Chapter 9. AMORPHOUS CARBON THIN FILMS

S. R. P. Silva, J. D. Carey, R. U. A. Khan, E. G. Gerstner, J. V. Anguita

1. Introduction	404
1.1. Carbon and Its Allotropes	405
1.2. Historical Perspective	408
1.3. Future Applications	408

2.	Deposition and Growth	409
2.1.	Deposition Techniques	409
2.2.	Growth Models	416
3.	Microstructure	420
3.1.	Experimental Determination of Microstructure	420
3.2.	Computer Modelling of Growth and Structure	424
4.	Optical Properties	432
4.1.	Introduction	432
4.2.	Infrared Absorption Studies	435
4.3.	Photoluminescence Spectroscopy	441
4.4.	Raman Spectroscopy	446
4.5.	Conclusions	455
5.	Defect Studies of Amorphous Carbon	455
5.1.	Introduction	455
5.2.	Lineshape Analysis and Relaxation Effects	456
5.3.	g Values	457
5.4.	Spin Densities	458
5.5.	Linewidths, Lineshapes, and Relaxation Effects	460
5.6.	Effects of Nitrogenation	463
5.7.	Effects of Annealing	464
5.8.	Correlation Energies and Photoyield Measurements	465
5.9.	Defects and Nonradiative Recombination	467
5.10.	Summary	467
6.	Electrical Properties of Amorphous Carbon	467
6.1.	Conduction and Amorphous Semiconductors	467
6.2.	Electronic Band Structure of Amorphous Materials	468
6.3.	Comparison with Amorphous Silicon	468
6.4.	Generalized Conduction in Amorphous Materials: Low Field Conduction	469
6.5.	High Field Conduction	470
6.6.	Electronic Structure and Properties of Amorphous Carbon	471
6.7.	Electronic Properties: GAC Films	472
6.8.	Electronic Properties: DAC Films	473
6.9.	Electronic Properties: TAC Films	475
6.10.	Electronic Modification of Amorphous Carbon	478
6.11.	Summary	481
7.	Concepts of Localization and Delocalization in a -C	482
7.1.	Ion Implantation of a -C	483
8.	Electron Field Emission	484
8.1.	Introduction	484
8.2.	Theory of Field Emission	484
8.3.	Planar Emitter Structures Based on Carbon	486
8.4.	Modelling of the Electron Emission Process	492
8.5.	Field Emission as a Function of Surface Modifications	496
9.	Amorphous Carbon-Based Devices	498
9.1.	Electronic Devices	498
9.2.	Novel Devices: Nonvolatile Memories, Antifuses, and MIMs	499
9.3.	Solar Cells	500
9.4.	Summary	500
10.	Conclusion	501
	References	501

Chapter 10. HIGH- T_c SUPERCONDUCTOR THIN FILMS

B. R. Zhao

1.	Introduction	507
2.	Fabrication of High- T_c Superconductor Thin Films	509
2.1.	Methods of Fabrication	509
2.2.	Substrate and Buffers	518
3.	High-Temperature Superconductor Thin Films	522
3.1.	$\text{YBa}_2\text{Cu}_3\text{O}_{7-\delta}$ (Y-123) and Related Materials Thin Films	522

3.2.	Bi ₂ Sr ₂ Ca _{n-1} Cu _n O _y System Thin Films	538
3.3.	La ₂ CuO ₄ System Thin Films	543
3.4.	TlBaCaCuO Thin Films	547
3.5.	Hg-Based Cuprate Thin Films	552
3.6.	Infinite CuO ₂ Layer Thin Films	554
3.7.	Ba _{1-x} K _x BiO ₃ (BKBO) System Thin Films	560
3.8.	Thin Films Related to C ₆₀	563
3.9.	Ultrathin Films and Multilayers	564
3.10.	Large-Area Thin Films	570
4.	Transport Properties in High- <i>T_c</i> Superconductor Thin Films	576
4.1.	Introduction	576
4.2.	Transport Properties	577
4.3.	Optical Properties	590
4.4.	Conclusion	594
5.	Device Applications	594
5.1.	Josephson Junctions and Superconducting Quantum Interference Devices	594
5.2.	Microwave Devices	598
6.	Heterostructures	605
6.1.	High- <i>T_c</i> Superconductor/Ferroelectric Heterostructures	605
6.2.	High- <i>T_c</i> Superconductor/CMR Material Heterostructures	610
7.	Conclusion	613
	Acknowledgments	614
	References	614

Chapter 11. ELECTRONIC AND OPTICAL PROPERTIES OF STRAINED SEMICONDUCTOR FILMS OF GROUPS IV AND III-V MATERIALS

George Theodorou

1.	Introduction	625
1.1.	Strain Tensor	627
2.	Deformation Potentials	627
2.1.	Γ Point States	627
2.2.	Indirect Conduction-Band Minima	628
2.3.	Optical Gaps E_1 and $E_1 + \Delta_1$	629
3.	The Tight-Binding Model	629
4.	Strained Si	630
4.1.	Biaxial Strain	630
4.2.	Uniaxial Strain	632
5.	Strained Ge	632
5.1.	Biaxial Strain	633
5.2.	Uniaxial Strain	634
6.	Strained Si _{1-x} Ge _x Alloys	635
6.1.	Optical Properties	636
7.	Strained Si _{1-y} C _y Alloys	637
7.1.	Optical Properties	638
8.	Si/Ge Superlattices	638
8.1.	Interface Intermixing	640
9.	Strained GaAs and InP	641
9.1.	GaAs	641
9.2.	InP	642
10.	InAs/AlSb Superlattices	642
10.1.	Electronic Properties	644
10.2.	Optical Properties	645
11.	Summary	645
	References	646

Chapter 12. GROWTH, STRUCTURE, AND PROPERTIES OF PLASMA-DEPOSITED AMORPHOUS HYDROGENATED CARBON-NITROGEN FILMS

D. F. Franceschini

1. Introduction	649
2. Amorphous Hydrogenated Carbon Films	650
2.1. a-C:H Film Structure	650
2.2. a-C:H Film Deposition	651
3. Nitrogen Incorporation Into a-C:H Films	654
3.1. Determination of Chemical Composition	654
3.2. Nitrogen Incorporation and Growth Kinetics	655
3.3. Plasma and Surface Processes Affecting Film Growth	658
3.4. Modeling of a-C(N):H Film Growth	661
4. Characterization of a-C(N):H Film Structure	663
4.1. Raman Spectroscopy	663
4.2. Infrared Spectroscopy	665
4.3. Electron Energy Loss Spectroscopy	666
4.4. X-Ray Photoelectron Spectroscopy	666
4.5. ¹³ C Nuclear Magnetic Resonance Spectroscopy	669
4.6. Overall Discussion	669
5. Mechanical Properties	670
5.1. Hardness and Stress	670
5.2. Friction and Wear	672
6. Optical and Electrical Properties	672
6.1. Optical Properties and Electron Spin Resonance	673
6.2. Electrical Properties	674
References	675

Chapter 13. CONDUCTIVE METAL OXIDE THIN FILMS

Quanxi Jia

1. Transparent Conducting Oxides	677
1.1. Different TCO Materials	677
1.2. Figure of Merit for TCOs	678
1.3. Deposition Techniques	679
1.4. Epitaxial Growth of ITO Films	681
1.5. Etching ITO Films	682
2. Ruthenium Oxide	682
2.1. Deposition Techniques	682
2.2. <i>Epitaxial Growth of RuO₂ Films</i>	683
2.3. Etching RuO ₂ Films	685
2.4. Applications of RuO ₂ Thin Films	686
3. Iridium Oxide	686
3.1. Deposition Techniques	686
3.2. Applications of IrO ₂ Films	688
4. Strontium Ruthenate	688
4.1. Deposition Techniques	688
4.2. Applications of SrRuO ₃ Films	689
4.3. Other Conductive Ruthenates	691
5. Strontium-Doped Lanthanum Cobaltite	692
5.1. Deposition Techniques	692
5.2. Oriented La _{0.5} Sr _{0.5} CoO ₃ Films on SiO ₂ /Si	693
5.3. Applications of La _{0.5} Sr _{0.5} CoO ₃ Films	695
6. Concluding Remarks	695
References	696
Index	699